

Inventor: Janos Fucsko et al.

Title: Wet Etching Method of Removing Silicon From a Substrate and
Method of Forming Trench Isolation

Assignee: Micron Technology, Inc.

INFORMATION DISCLOSURE STATEMENT

References -- See Attached Form PTO-1449

The attached form PTO-1449 is submitted in compliance with
37 CFR § 1.56. Copies of the cited art are included. No admission is made
regarding whether all the submitted references are prior art.

Respectfully submitted,

Dated: 7-22-03

Attorney: 

Mark S. Matkin
Reg. No. 32,268

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY. DOCKET NO. M122-2246		SERIAL NO. Unknown	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)					APPLICANT: Janos Fucsko et al.			
					FILING DATE Filed Herewith		GROUP Unknown	
U.S. PATENT DOCUMENTS								
*Examiner's Initials		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
	AA							
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		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
	AJ							
	AK							
	AL							
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
	AM		Bertagna et al., <i>Ionic components dependence of the charge transfer reactions at the silicon / HF solution</i> <i>Interface</i> , 4 J. SOLID STATE ELECTROCHEM. 42-51 (1999).					
	AN							
	AO							
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<p>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>								